

IN THE ABSTRACT

Change the paragraph beginning at Page 25, line 4 to read as follows:

1       - - To form a spin valve device, start by forming a gap layer. Form a buffer layer with a layer of  
2 refractory material on the buffer layer. Form patterned underlayers including a magnetic material for  
3 providing trackwidth and longitudinal bias on the buffer layer comprising either a lower  
4 antiferromagnetic layer stacked with a ferromagnetic layer or a Cr layer stacked with a permanent  
5 magnetic layer. Form an inwardly tapered depression in the patterned underlayers down to the buffer  
6 layer by either ion milling through a mask or a stencil lift off technique. Form layers covering the  
7 patterned underlayers that cover the inwardly tapered depression. Form free, pinned, spacer and  
8 antiferromagnetic layers. Form conductors either on a surface of the antiferromagnetic layer aside from  
9 the depression or between the buffer layer and the patterned underlayers. - -